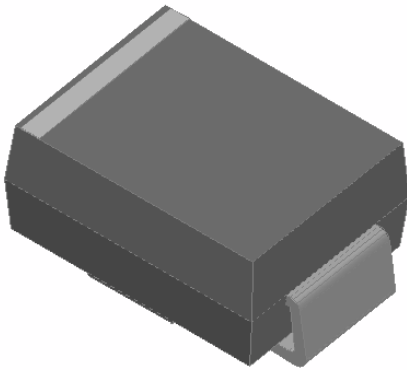


G i fZUWY' A c i b h' G i dYf' : Ugh' FYWc jYfm' FYWhjZjYf'

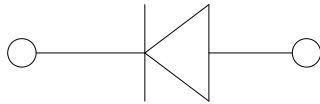


..... :YU h i fYg''''

- Low profile package
- Ideal for automated placement
- Glass passivated chip junction
- High forward surge capability
- Super Fast reverse recovery time
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

..... HmdjWU'' 5dd' jWUh]cbg'

For use in high frequency rectification of power supplies, inverters, converters, and freewheeling diodes for consumer and telecommunication.



.. 'AYW\UbjWU'' 8U hU'

- DUW_U[Y: DO-214AA (SMB)
- Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- HYf a]bU'g': Tin plated leads, solderable per J-STD-002 and JESD22-B102
- Dc'Uf]hm.' Cathode line denotes the cathode end

AU l]a i a 'FU h]b [g (T_a=25 Unless otherwise specified

D5F5A9H9F'	GMA6C@'	IB-H	I ; '56	I ; '66	I ; '76	I ; '86	I ; ' :6'	I ; ' ;6'	I ; '<6	I ; '>6
Device marking code			UG3AB	UG3BB	UG3CB	UG3DB	UG3FB	UG3GB	UG3HB	UG3JB
Maximum Repetitive Peak Reverse Voltage	VRRM	V	50	100	150	200	300	400	500	600
Maximum RMS Voltage	VRMS	V	35	70	105	140	210	280	350	420
Maximum DC blocking Voltage	VDC	V	50	100	150	200	300	400	500	600
Average rectified output current @60Hz sine wave, resistance load, TL (Fig.1)	I _O	A	3.0							
Forward Surge Current (Non-repetitive) @60Hz Half-sine wave, 1 cycle, T _j =25	I _{FSM}	A	100							
Forward Surge Current (Non-repetitive) @1ms, square wave, 1 cycle, T _j =25			200							
Current squared time @1ms t 8.3ms T _j =25	I ² t	A ² s	41.5							
Storage temperature	T _{stg}		-55 ~ +150							
Junction temperature	T _j		-55 ~ +150							



1 ; '56'H<F I' I ; '>6'

9'YWhf]WU' 7 \UfUWhYf]gh]Wg' $T_a=25$ Unless otherwise specified

D5F5A9H9F'	GMA6C@'	IB-H'	H9GH' 7CB8-H-CBG'	I ; '56	I ; '66	I ; '76	I ; '86'	I ; ':6'	I ; ' ; 6'	I ; '<6	I ; '>6
Maximum instantaneous forward voltage	V _F	V	I _{FM} =3.0A	0.92			1.25		1.7		
Maximum reverse recovery time	t _{rr}	ns	I _F =0.5A, I _R =1.0A, I _{rr} =0.25A	25					35		
Maximum DC reverse current at rated DC blocking voltage	I _R	μA	T _j =25	5							
			T _j =125	50							
Typical junction capacitance	C _j	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C	65			58		55		

8mbU a]W' 7 \UfUWhYf]gh]Wg' I ; '56'H<F I' I ; '86'

D5F5A9H9F'	GMA6C@'	IB-H'	H9GH' 7CB8-H-CBG'	A]b'	Hmd'	AUI'
Reverse Recovery Time	T _{RR}	ns	T _j =25	I _F =1A di/dt=-50A/us		30
			T _j =125			
Peak recovery current	I _{RRM}	A	T _j =25	I _F =3A di/dt=-200A/us V _{RM} =100V		3.8
			T _j =125		nCT	6.5
Reverse recovery charge	Q _{rr}	nC	T _j =25			39.9
			T _j =125			113.2
Non-repetitive avalanche energy	E _{AS}	mJ	T _j =25	I _B =3.6 A L _A =15 mH	116.6	-

I ; ':6'H<F I' I ; ' ; 6'

D5F5A9H9F'	IB-H'	AUI'
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Reverse Recovery Time T_{RR} $T_j=25$ ns $di/dt=-50A/us$ V



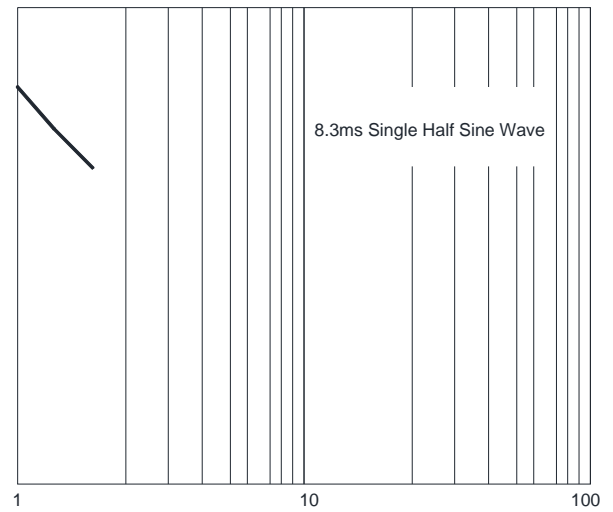
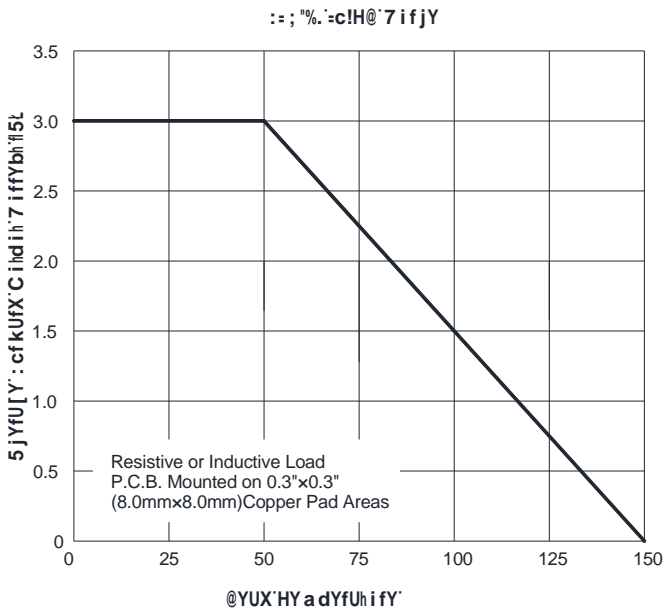
1 ; '56'H<F I' I ; '>6'

H\YfaU'7\UfUWhYf]gh]Wg' $T_a=25$ Unless otherwise specified

D5F5A9H9F'	GMA6C@'	IB-H'	I ; '56	I ; '66	I ; '76	I ; '86	I ; ':6'	I ; ';6'	I ; '<6	I ; '>6
Typical Thermal resistance	R J-A ⁽¹⁾	/W	65							
	R J-L ⁽¹⁾		20							
	R J-C ⁽¹⁾		18							

Note:
 (1) Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.3" x 0.3" (8.0 mm x 8.0 mm) copper pad areas

7\UfUWhYf]gh]Wg'(Typical)





CfXYf]b ['bzcf a Uh]cb' (Example)

DF9 : 9F98 'D#B'	D57 ?=B ; '7C89'	IB='K9= ; <Hfl [L'	A=B-A I A' D57 ? 5 ; 9fidWgt	=BB9F'6CL' E I 5BH=HMfidWgt	C I H9F'75FHCB' E I 5BH=HMfidWgt'	89@=J9FM' AC89'
I ; '56! I ; '>6	F1	Approximate 0.096	3000	/	48000	13" reel
I ; '56! I ; '>6	F2	Approximate 0.096	750	6000	24000	7" reel
I ; '56! I ; '>6	F3	Approximate 0.096	500	4000	16000	7" reel

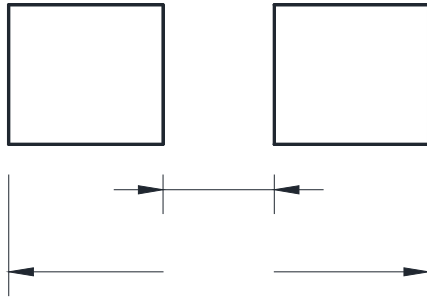
C i h`]bY' 8] a Ybg]cbg`

8C!&%(55fiGA6L'

Dim



'Gi [[YghYX'dUX''Umc i h'



Dimensions in millimeters

8C!&% (55fGA6L'	
Dim	Millimeters
P1	6.8
P2	4.3
P3	1.8
Q1'	2.5
Q2'	2.3



I ; '56'H<F I ' I ; '>6'

8]gW'U]a Yf'